

Features

- Low saturation voltage
- High current capability
- Low switching loss
- Low static and peak forward voltage drop free-wheeling diode

Applications

- Induction cooking, microwave oven
- Soft switching application

Description

This IGBT utilizes the advanced PowerMESH™ process resulting in an excellent trade-off between switching performance and low on-state behavior. This device is well suited for the resonant or soft switching applications.

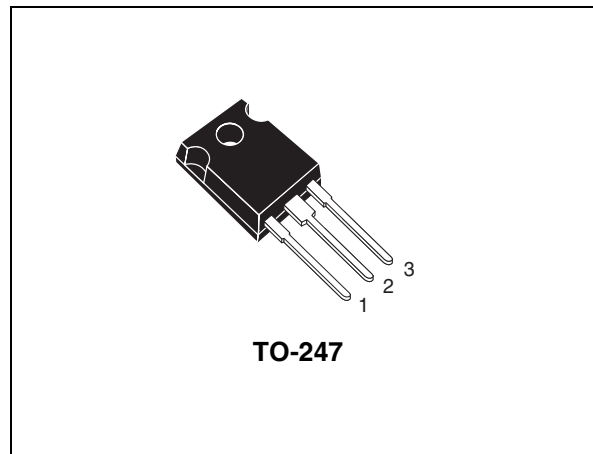


Figure 1. Internal schematic diagram

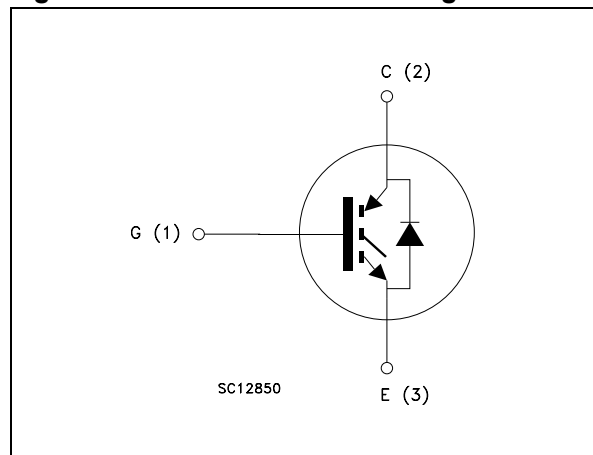


Table 1. Device summary

Order codes	Marking	Package	Packaging
STGW38IH130D	GW38IH130D	TO-247 long leads	Tube
STGWS38IH130D		TO-247	

Contents

1	Electrical ratings	3
2	Electrical characteristics	4
	2.1 Electrical characteristics (curves)	6
3	Test circuits	8
4	Package mechanical data	9
5	Revision history	12

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value		Unit
		TO-247 long leads	TO-247	
V _{CES}	Collector-emitter voltage (V _{GE} = 0)	1300		V
I _C ⁽¹⁾	Continuous collector current at T _C = 25 °C	63	55	A
I _C ⁽¹⁾	Continuous collector current at T _C = 100 °C	33	25	A
I _{CL} ⁽²⁾	Turn-off latching current	40		A
I _{CP} ⁽³⁾	Pulsed collector current	125		A
V _{GE}	Gate-emitter voltage	±25		V
P _{TOT}	Total dissipation at T _C = 25 °C	250	180	W
I _F	Diode RMS forward current at T _C = 25 °C	30		A
I _{FSM}	Surge non repetitive forward current t _p = 10 ms sinusoidal	100		A
T _j	Operating junction temperature	-55 to 150		°C

1. Calculated according to the iterative formula:

$$I_C(T_C) = \frac{T_{j(max)} - T_C}{R_{thj-c} \times V_{CE(sat)(max)}(T_{j(max)}, I_C(T_C))}$$

2. V_{clamp} = 960 V, T_j = 150 °C, R_G = 10 Ω, V_{GE} = 15 V

3. Pulse width limited by maximum permissible junction temperature and turn-off within RBSOA

Table 3. Thermal data

Symbol	Parameter	Value		Unit
		TO-247 long leads	TO-247	
R _{thj-case}	Thermal resistance junction-case IGBT	0.5	0.7	°C/W
R _{thj-case}	Thermal resistance junction-case diode	2	2.1	°C/W
R _{thj-amb}	Thermal resistance junction-ambient	50		°C/W

2 Electrical characteristics

($T_J = 25\text{ °C}$ unless otherwise specified)

Table 4. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage ($V_{GE} = 0$)	$I_C = 1\text{ mA}$	1300			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}, I_C = 20\text{ A}$ $V_{GE} = 15\text{ V}, I_C = 20\text{ A}, T_J = 125\text{ °C}$		2.1 2.0	2.8	V V
$V_{GE(th)}$	Gate threshold voltage	$V_{CE} = V_{GE}, I_C = 1\text{ mA}$	3.75		5.75	V
I_{CES}	Collector-cut-off current ($V_{GE} = 0$)	$V_{CE} = 1300\text{ V}$ $V_{CE} = 1300\text{ V}, T_J = 125\text{ °C}$			1 10	mA mA
I_{GES}	Gate-emitter leakage current ($V_{CE} = 0$)	$V_{GE} = \pm 20\text{ V}$			± 100	nA
$g_{fs}^{(1)}$	Forward transconductance	$V_{CE} = 25\text{ V}, I_C = 20\text{ A}$		20		S
V_F	Diode forward voltage	$I_F = 20\text{ A}$ $I_F = 20\text{ A}, T_J = 125\text{ °C}$		1.3	1.9 1.7	V V

1. Pulsed: pulse duration= 300 μ s, duty cycle 1.5%

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{ies}	Input capacitance	$V_{CE} = 25\text{ V}, f = 1\text{ MHz}, V_{GE} = 0$	-	2900	-	pF
C_{oes}	Output capacitance			155		
C_{res}	Reverse transfer capacitance			30		
Q_g	Total gate charge	$V_{CE} = 960\text{ V},$ $I_C = 20\text{ A}, V_{GE} = 15\text{ V}$	-	127	-	nC
Q_{ge}	Gate-emitter charge			18		
Q_{gc}	Gate-collector charge			50		

Table 6. Inductive load switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_r(V_{off})$	Off voltage rise time	$V_{CC} = 960\text{ V}$, $I_C = 20\text{ A}$ $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$, (see Figure 15)	-	102	-	ns
$t_{d(off)}$	Turn-off delay time			284		ns
t_f	Current fall time			180		ns
$t_r(V_{off})$	Off voltage rise time	$V_{CC} = 960\text{ V}$, $I_C = 20\text{ A}$ $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$, $T_J = 125\text{ }^\circ\text{C}$ (see Figure 15)	-	200	-	ns
$t_{d(off)}$	Turn-off delay time			424		ns
t_f	Current fall time			316		ns

Table 7. Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$E_{off}^{(1)}$	Turn-off switching losses	$V_{CC} = 960\text{ V}$, $I_C = 20\text{ A}$ $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$, (see Figure 15)	-	3.4	-	mJ
$E_{off}^{(1)}$	Turn-off switching losses			6.4		mJ

1. Turn-off losses include also the tail of the collector current

2.1 Electrical characteristics (curves)

Figure 2. Output characteristics

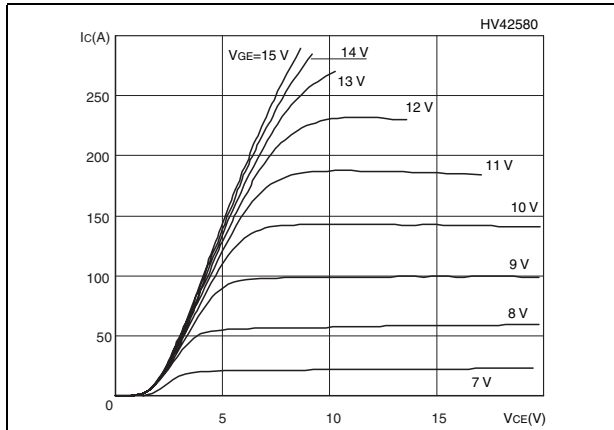


Figure 3. Transfer characteristics

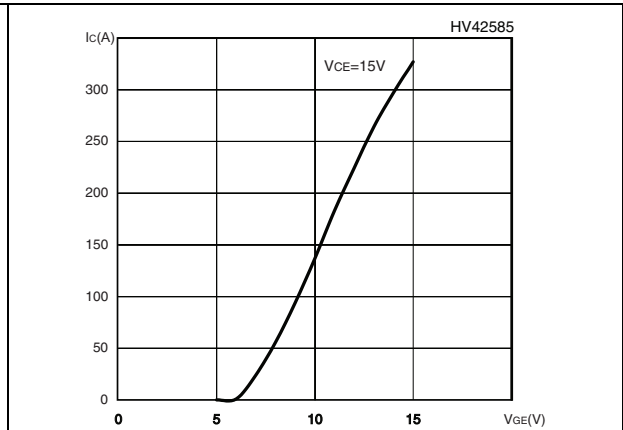


Figure 4. Transconductance

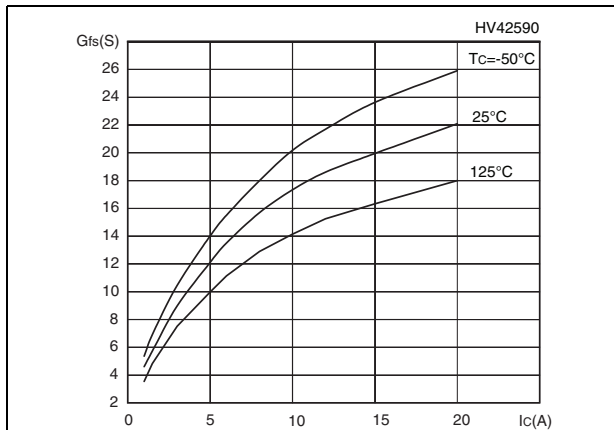


Figure 5. Collector-emitter on voltage vs temperature

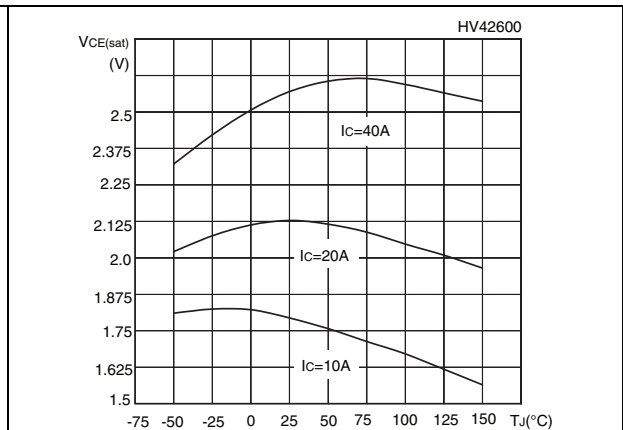


Figure 6. Normalized breakdown voltage vs temperature

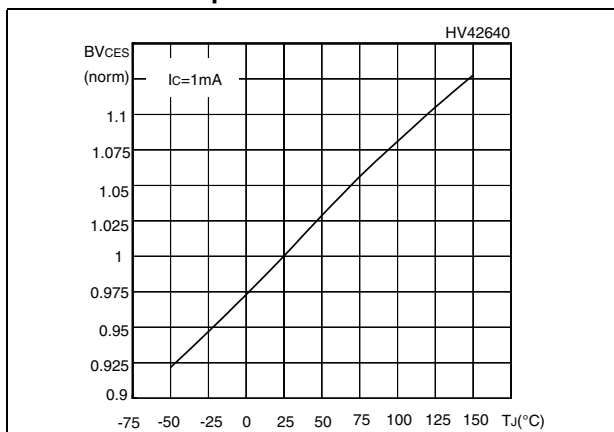


Figure 7. Gate-charge vs gate-emitter

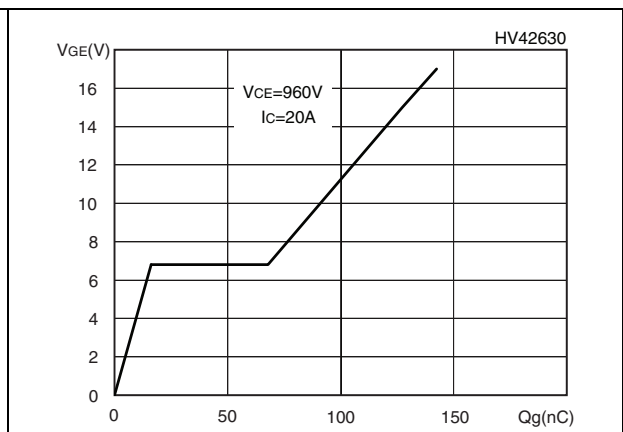


Figure 8. Normalized gate threshold voltage vs temperature

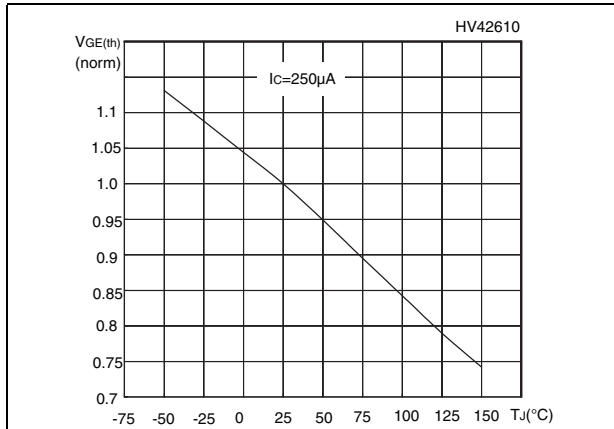


Figure 9. Collector-emitter on voltage vs collector current

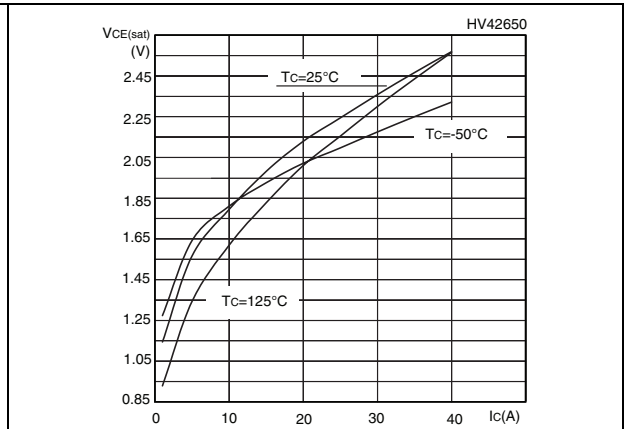


Figure 10. Switching losses vs temperature

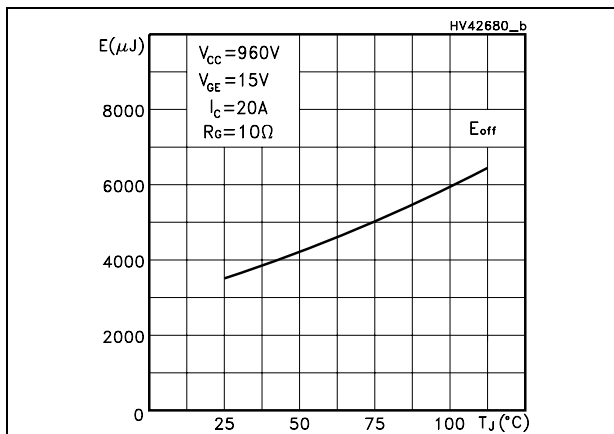


Figure 11. Switching losses vs gate resistance

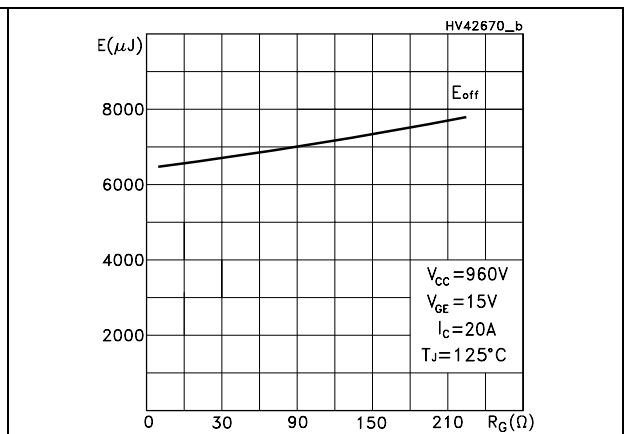


Figure 12. Switching losses vs collector current

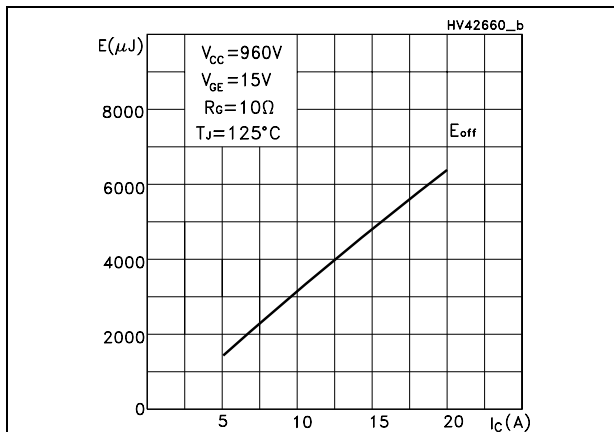


Figure 13. RBSOA

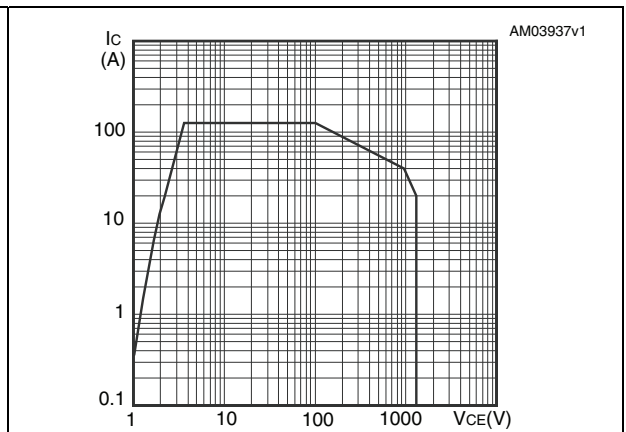
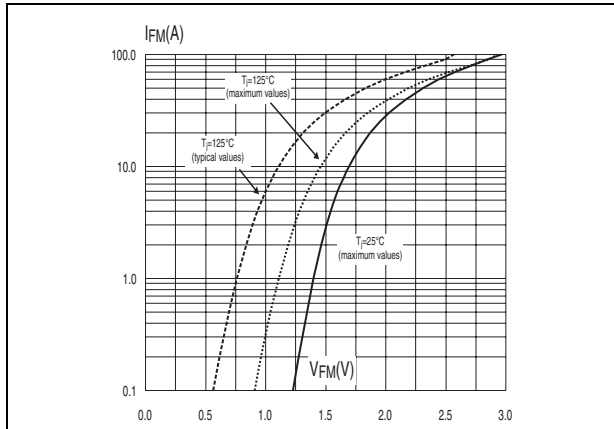


Figure 14. Emitter-collector diode characteristics



3 Test circuits

Figure 15. Test circuit for inductive load switching

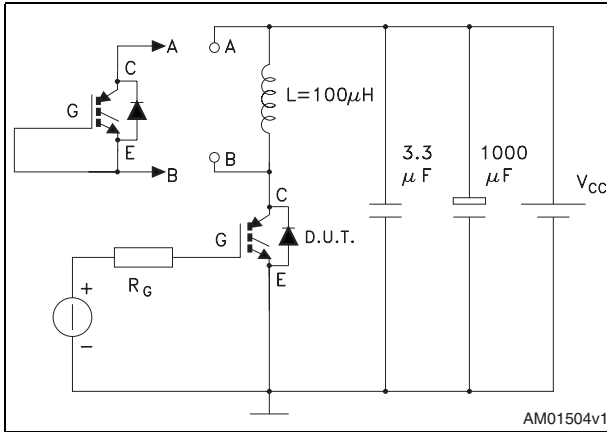


Figure 16. Gate charge test circuit

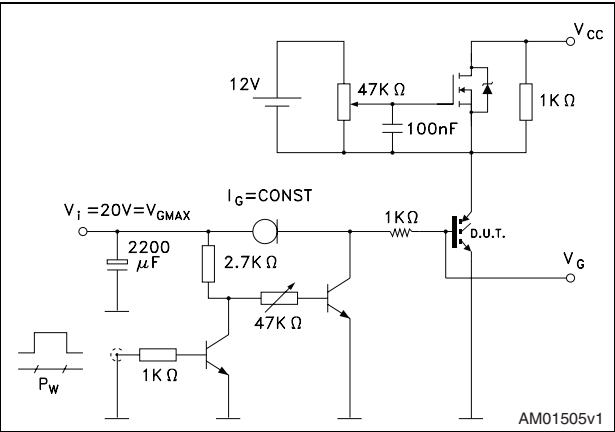
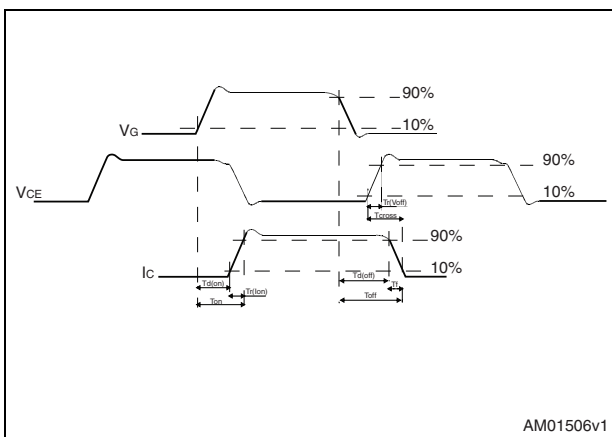


Figure 17. Switching waveform

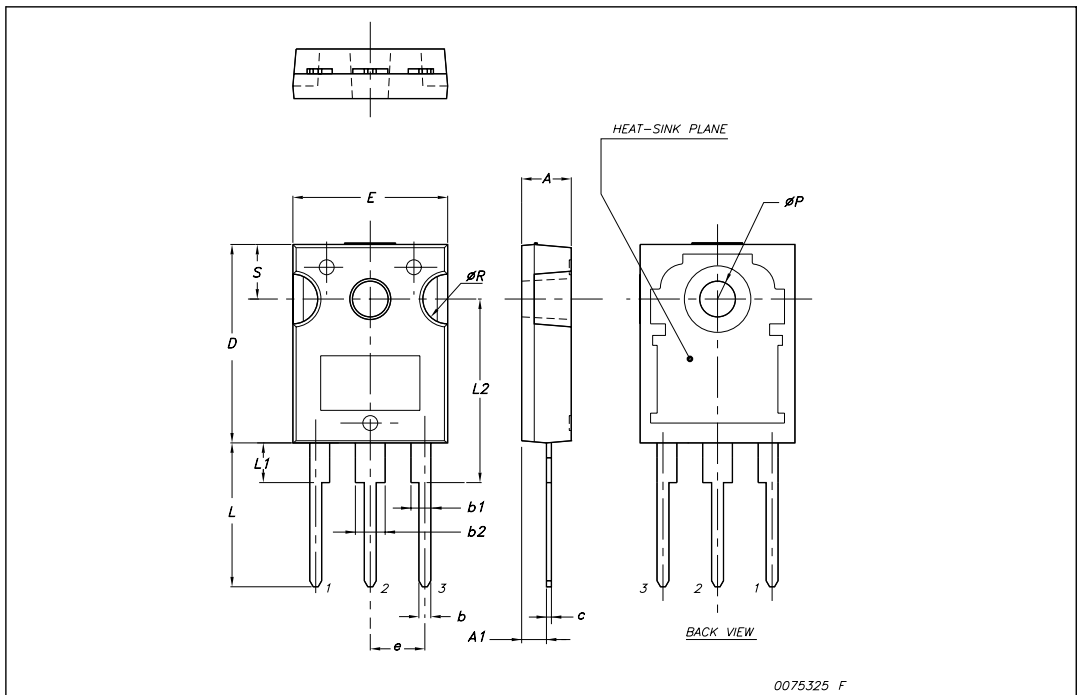


4 Package mechanical data

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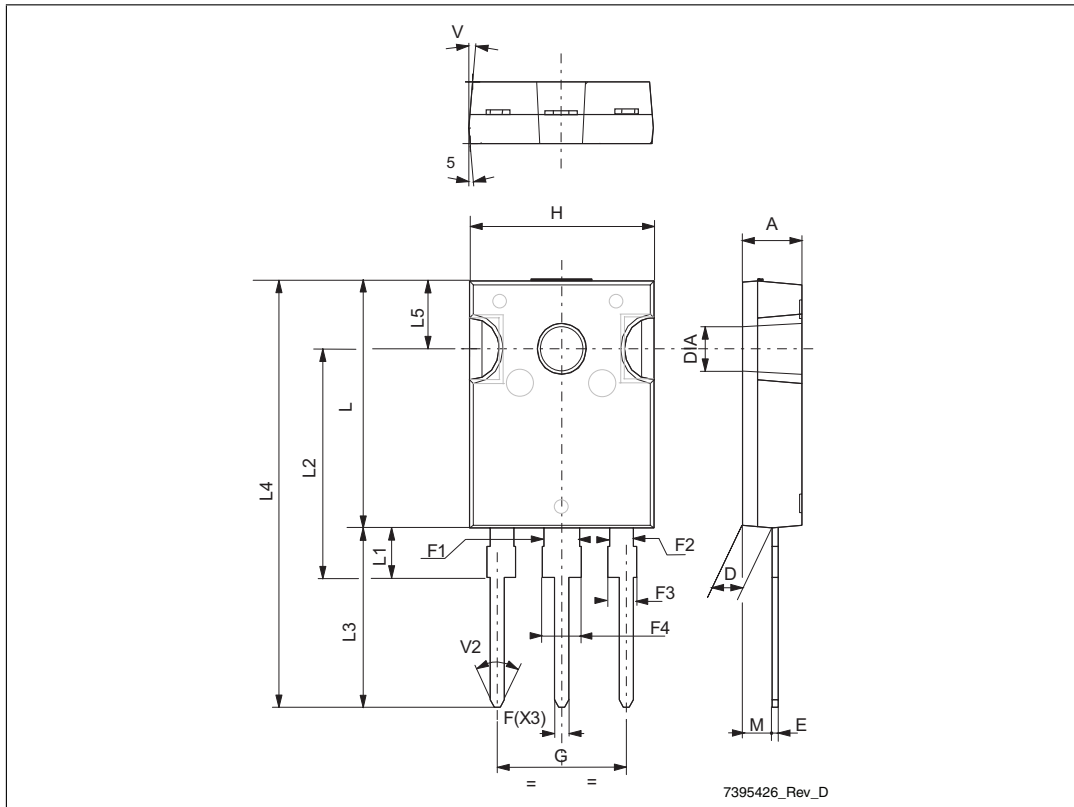
TO-247 Mechanical data

Dim.	mm.		
	Min.	Typ	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e		5.45	
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
∅P	3.55		3.65
∅R	4.50		5.50
S		5.50	



TO-247 long leads mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.85		5.16
D	2.2		2.6
E	0.4		0.8
F	1		1.4
F1		3	
F2		2	
F3	1.9		2.4
F4	3		3.4
G		10.9	
H	15.45		16.03
L	19.85		21.09
L1	3.7		4.3
L2	18.3		19.13
L3	14.2		20.3
L4	34.05		41.38
L5	5.35		6.3
M	2		3
V		5°	
V2		60°	
DIAM	3.55		3.65



5 Revision history

Table 8. Document revision history

Date	Revision	Changes
11-May-2009	1	Initial release
16-Jul-2009	2	Document status promoted from preliminary data to datasheet.

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